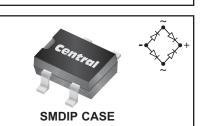
CBR1-D020S SERIES

SURFACE MOUNT 1 AMP SILICON BRIDGE RECTIFIER





www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1-D020S series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

NOTE: Also available in Fast Recovery, please contact factory for details.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T _A =25°C unless otherwise noted)	SYMBOL	CBR1- D020S	CBR1- <u>D040S</u>	CBR1- D060S	CBR1- D080S	CBR1- D100S	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_{R}	200	400	600	800	1000	V
RMS Reve	V _{R(RMS)}	140	280	420	560	700	V
Average Forward Current (T _A =50°C)	IO			1.0			Α
Peak Forward Surge Current	IFSM			50			Α
Rating for Fusing (t<8.35ms)	I ² t			10			A^2s
Operating and Storage Junction Temperature	T _{.J} , T _{sta}			-65 to +150)		°C

ELECTRICAL CHARACTERISTICS PER DIODE: (TA=25°C unless otherwise noted)

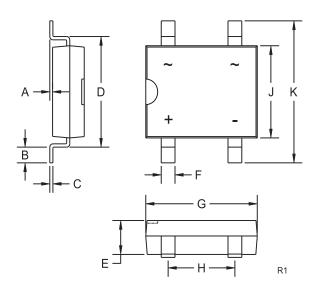
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{R}	V_{R} =Rated V_{RRM}			10	μΑ
I_{R}	V _R =Rated V _{RRM} , T _A =125°C			0.5	mA
V_{F}	I _F =1.0A			1.1	V
CJ	V _R =4.0V, f=1.0MHz		25		pF

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SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS						
	INC	HES	MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
А	0.004	0.008	0.10	0.20		
В	0.040	0.060	1.02	1.52		
С	0.009		0.23			
D	0.290	0.310	7.37	7.87		
Е	0.086	0.098	2.18	2.49		
F	0.038	0.042	0.97	1.07		
G	0.316	0.335	8.03	8.51		
Н	0.195	0.205	4.95	5.21		
J	0.245	0.255	6.22	6.48		
K	0.360	0.410	9.14	10.41		

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R3 (4-January 2010)